THE 6JH6 IS A SEMIREMOTE-CUTOFF PENTODE IN THE 7 PIN MINIATURE CONSTRUCTION. IT IS INTENDED FOR USE IN THE GAIN-CONTROLLED PICTURE-IF AMPLIFIER STAGES OF TELEVISION RECEIVERS. BECAUSE OF ITS CONTROLLED SEMIREMOTE-CUTOFF CHARACTERISTIC, THE 6JH6 CAN SUBSTANTIALLY REDUCE THE EFFECTS OF CROSS MODULATION IN THE IF STAGES OF COLOR T.V. RECEIVERS.

DIRECT INTERELECTRODE CAPACITANCES

<table>
<thead>
<tr>
<th></th>
<th>WITHOUT SHIELD</th>
<th>WITH SHIELD NO. 316 CONNECTED TO CATHODE</th>
</tr>
</thead>
<tbody>
<tr>
<td>GRID 1 TO PLATE</td>
<td>MAX. 0.025</td>
<td>MAX. 0.015 pf</td>
</tr>
<tr>
<td>GI TO (H + K + G2 + G3 + I.S.)</td>
<td>7 pf</td>
<td>7 pf</td>
</tr>
<tr>
<td>P TO (H + K + G2 + G3 + I.S.)</td>
<td>2 pf</td>
<td>3 pf</td>
</tr>
</tbody>
</table>

HEATER CHARACTERISTICS AND RATINGS

DESIGN MAXIMUM VALUES - SEE EIA STANDARD RS-229

<table>
<thead>
<tr>
<th></th>
<th>6.3 VOLTS</th>
<th>300 MA.</th>
</tr>
</thead>
<tbody>
<tr>
<td>LIMITS OF APPLIED VOLTAGE</td>
<td>6.3 ± 0.6</td>
<td>VOLTS</td>
</tr>
</tbody>
</table>

PEAK HEATER-CATHODE VOLTAGE:
- HEATER NEGATIVE WITH RESPECT TO CATHODE 200 VOLTS
- HEATER POSITIVE WITH RESPECT TO CATHODE 200 VOLTS
- DC COMPONENT 100 VOLTS

CONTINUED ON FOLLOWING PAGE
CONTINUED FROM PRECEDING PAGE

MAXIMUM RATINGS
DESIGN MAXIMUM VALUES - SEE EIA STANDARD RS-239
CLASS AI AMPLIFIER

PLATE VOLTAGE 300 VOLTS
GRID 3 VOLTAGE 0 VOLTS
GRID 2 SUPPLY VOLTAGE 300 VOLTS
GRID 2 VOLTAGE SEE RATING CHART
GRID 1 VOLTAGE
  POSITIVE BIAS VALUE 0 VOLTS
GRID 2 INPUT
  FOR GRID 2 VOLTAGES UP TO 150 VOLTS 0.55 VOLTS
  FOR GRID 2 VOLTAGES BETWEEN 150 AND 300 VOLTS SEE RATING CHART
PLATE DISSIPATION
GRID 1 CIRCUIT RESISTANCE:
  FOR FIXED-BIAS OPERATION MAX. 0.25 MEGOHM
  FOR CATHODE-BIAS OPERATION MAX. 1 MEGOHM

CHARACTERISTICS
CLASS AI AMPLIFIER

PLATE VOLTAGE 125 VOLTS
GRID 3 VOLTAGE - CONNECTED TO CATHODE AT SOCKET 125 VOLTS
GRID 2 VOLTAGE 56 OHMS
CATHODE RESISTOR 14 MA.
PLATE CURRENT 3.6 MA.
GRID 2 CURRENT 8,000 µMHOSES
TRANSCONDUCTANCE APPROX. 0.26 MEGOHM
PLATE RESISTANCE

GRID 1 VOLTAGE FOR $g_m = 50$ µMHOSES -19 VOLTS
TRANSCONDUCTANCE RANGE AT $E_{C1} = 4.5$ V. AND $R_k = 56$ Ω 400-900 µMHOSES
AVERAGE CHARACTERISTICS

$E_b = 125$ VOLTS
$E_c = 0$ VOLTS

GRID 1 VOLTS

TRANSCELENTANCE ($G_m$) - MICROMHOS